

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P _D	0.7	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	Steady State	184
		t < 10s	115
Total Power Dissipation (Note 6)	P _D	1.3	W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	Steady State	94
		t < 10s	61
Thermal Resistance, Junction to Case	R _{θJC}	25	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Drain-Source Voltage	V _{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	±8	V
Continuous Drain Current (Note 6) V _{GS} = -4.5V	I _D	Steady State T _A = +25°C T _A = +70°C	3.0 2.4
		t < 10s T _A = +25°C T _A = +70°C	3.7 2.9
Continuous Drain Current (Note 6) V _{GS} = -2.5V	I _D	Steady State T _A = +25°C T _A = +70°C	2.5 2.0
		t < 10s T _A = +25°C T _A = +70°C	3.2 2.5
Maximum Continuous Body Diode Forward Current (Note 6)	I _S	1.9	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)	I _{DM}	20	A

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1.0	μA	V _{DS} = -16V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	-0.6	-0.55	-1.3	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	—	73	95	mΩ	V _{GS} = -4.5V, I _D = -3.0A
			95	130		V _{GS} = -2.5V, I _D = -2.6A
			146	190		V _{GS} = -1.8V, I _D = -1A
Forward Transfer Admittance	Y _{fs}	—	8	-	S	V _{DS} = -5V, I _D = -3A
Diode Forward Voltage	V _{SD}	—	-0.8	-1.25	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	857	—	pF	V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	54	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	49	—	pF	
Gate Resistance	R _g	—	12.3	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge	Q _g	—	9.0	—	nC	V _{GS} = -4.5V, V _{DS} = -15V, I _D = -4A
Gate-Source Charge	Q _{gs}	—	1.6	—	nC	
Gate-Drain Charge	Q _{gd}	—	1.1	—	nC	
Turn-On Delay Time	t _{D(on)}	—	9.7	—	ns	V _{DS} = -15V, V _{GS} = -10V, R _L = 15Ω, R _G = 6.0Ω, I _D = -1A
Turn-On Rise Time	t _r	—	17.7	—	ns	
Turn-Off Delay Time	t _{D(off)}	—	268.8	—	ns	
Turn-Off Fall Time	t _f	—	64.2	—	ns	

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

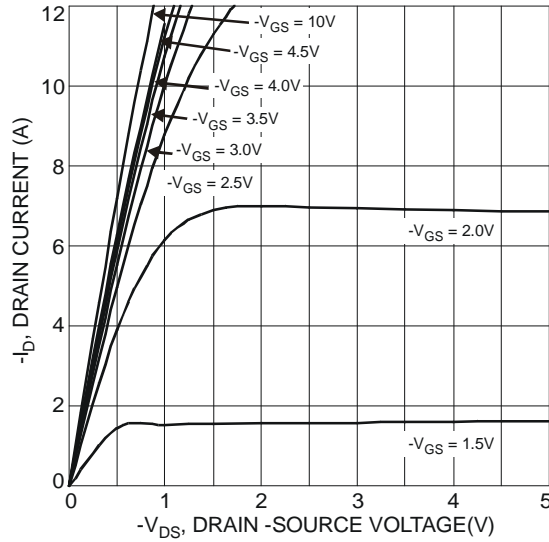


Fig. 1 Typical Output Characteristics

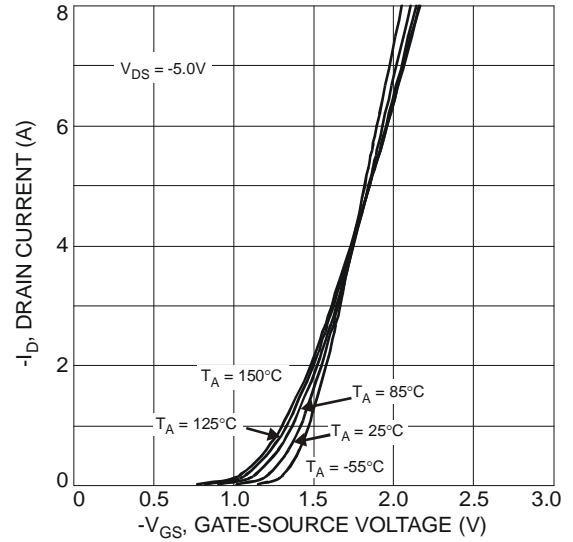


Fig. 2 Typical Transfer Characteristics

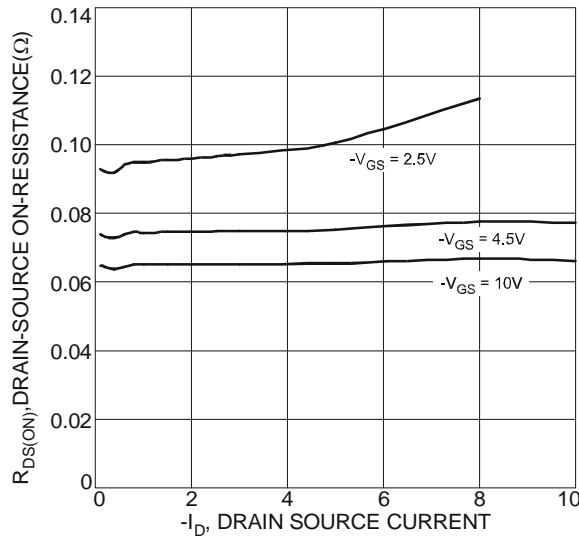


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

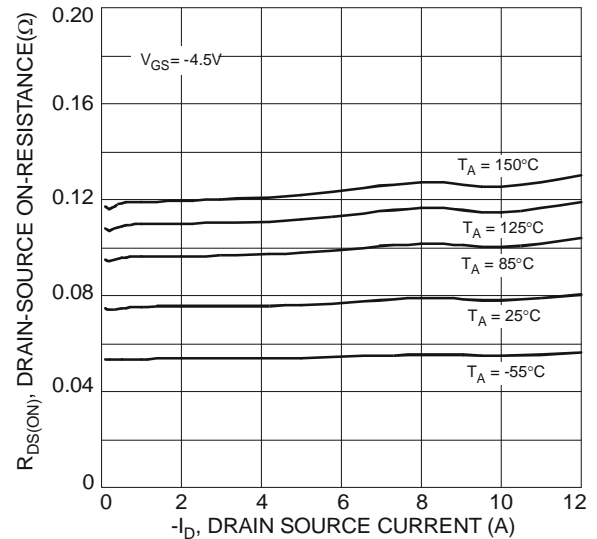


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

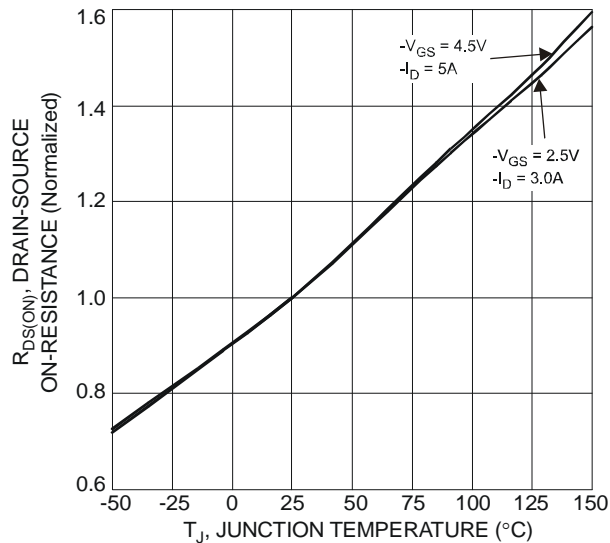


Fig. 5 On-Resistance Variation with Temperature

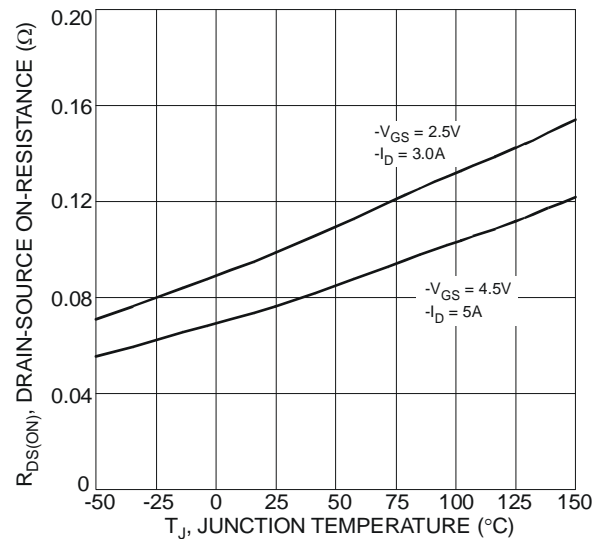


Fig. 6 On-Resistance Variation with Temperature

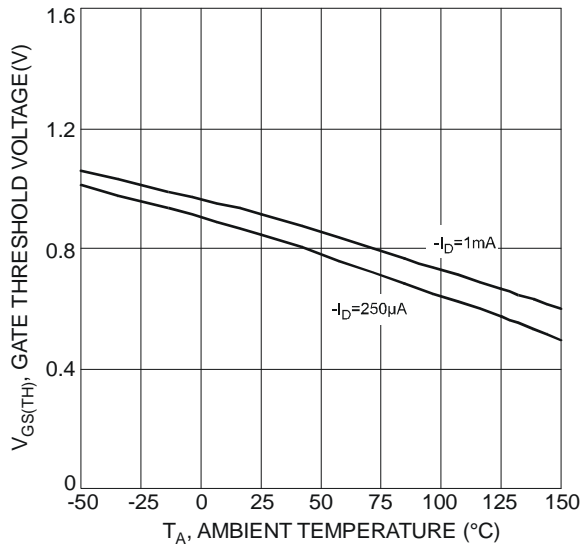


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

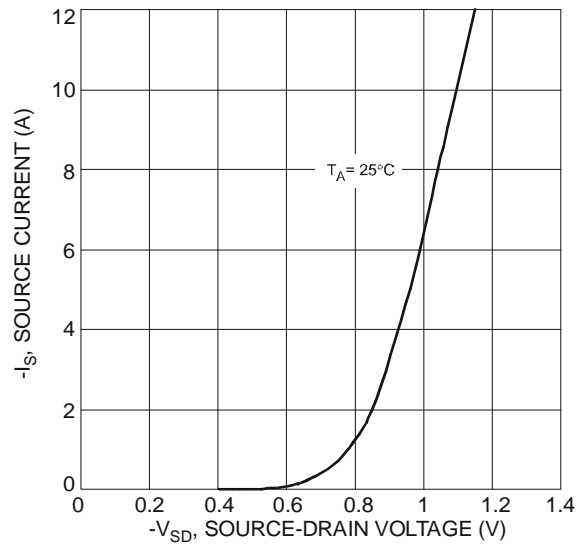


Fig. 8 Diode Forward Voltage vs. Current

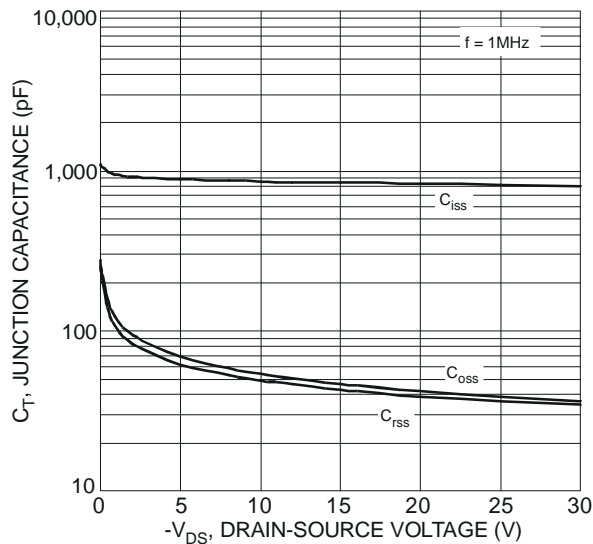


Fig. 9 Typical Junction Capacitance

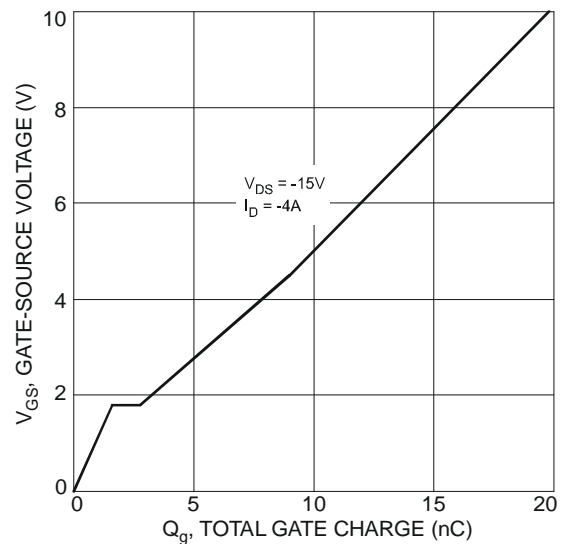


Fig. 10 Gate-Charge Characteristics

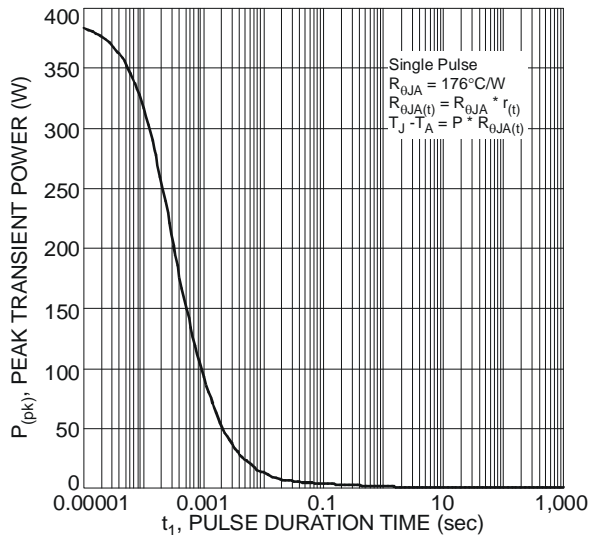


Fig. 11 Single Pulse Maximum Power Dissipation

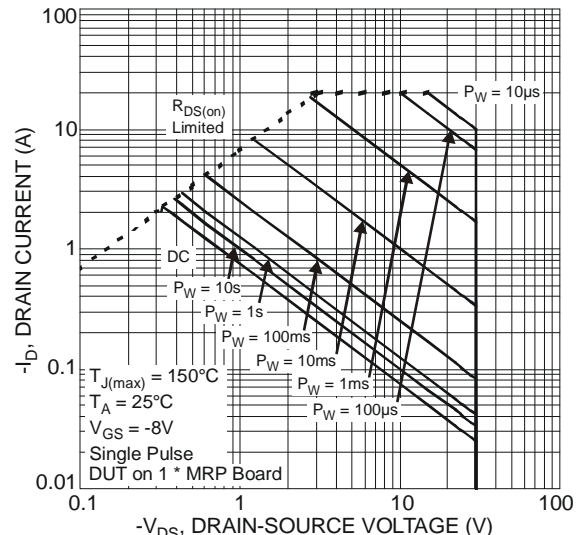
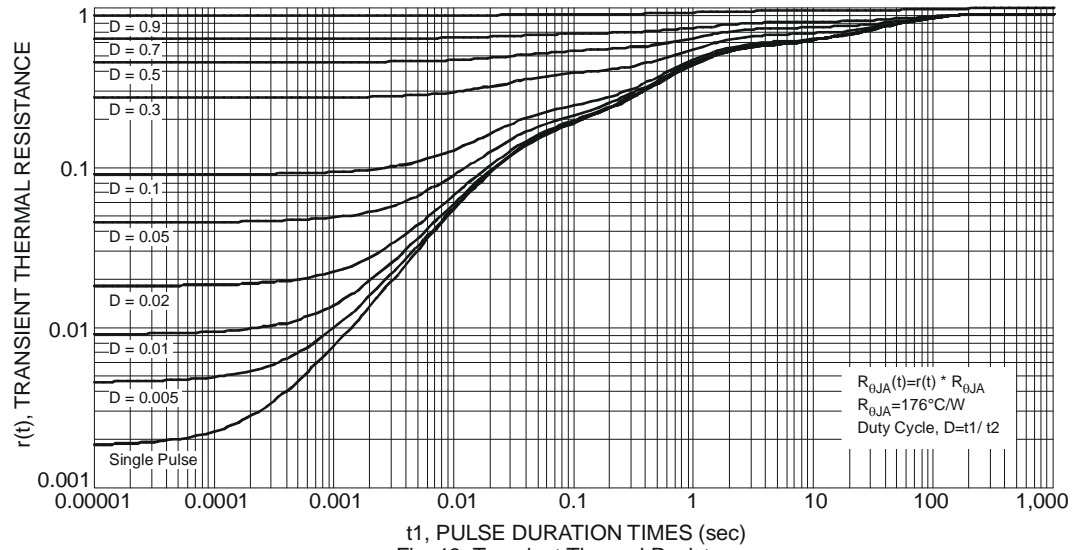
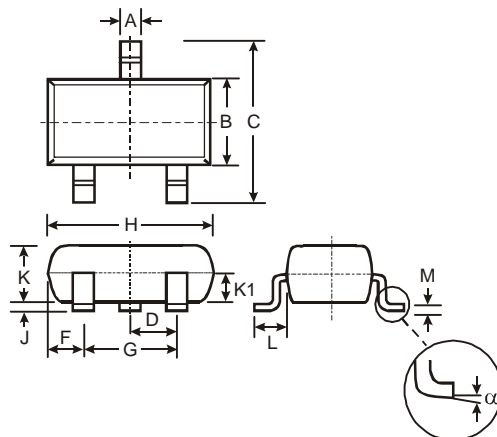


Fig. 12 SOA, Safe Operation Area



Package Outline Dimensions

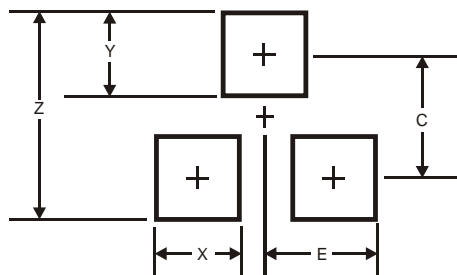
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35

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